



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	20mΩ @ V <sub>GS</sub> = 10V	6.9A
30V	$27m\Omega$ @ $V_{GS} = 4.5V$	5.8A

#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

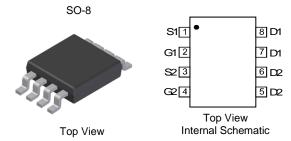
#### **Description**

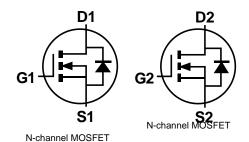
This MOSFET is designed to minimize the on-state resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
   Solderable per MIL-STD-202, Method 208<sup>(3)</sup>
- Weight: 0.072grams (Approximate)





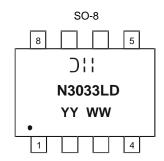
#### **Ordering Information (Note 5)**

Part Number	Case	Packaging
DMN3033LSDQ-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



O|| = Manufacturer's Marking N3033LD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 13 = 2013) WW = Week (01 - 53)



## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 6)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ID	6.9 5.8	А
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	30	А

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	$P_{D}$	2	W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C

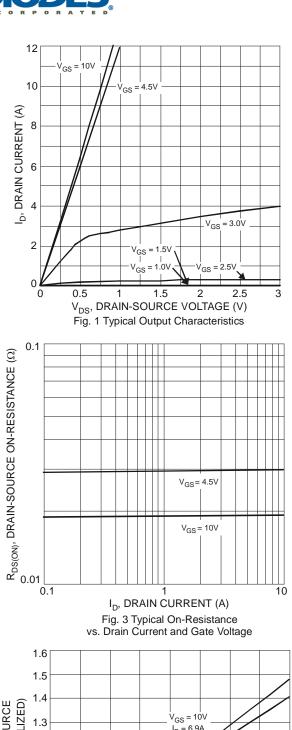
# **Electrical Characteristics** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

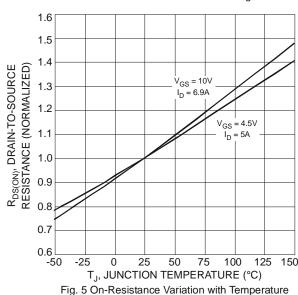
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	100	nA	$V_{DS} = 30V$ , $V_{GS} = 0V$	
Cata Sauras Laskaga		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	1	μΑ	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	1	2.1	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	7		13	20	mΩ	$V_{GS} = 10V, I_D = 6.9A$	
Static Dialif-Source Off-Resistance	R <sub>DS</sub> (ON)		22	27	11152	$V_{GS} = 4.5V, I_D = 5A$	
Forward Transconductance	g <sub>fs</sub>	_	7	_	S	$V_{DS} = 5V, I_D = 6.9A$	
Diode Forward Voltage (Note 8)	$V_{SD}$	0.5	_	1.2	V	$V_{GS} = 0V$ , $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	725	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	_	114	_	pF		
Reverse Transfer Capacitance	Crss	_	92	_	pF	I = IIVIHZ	
Gate Resistance	$R_{G}$	_	0.89	_	Ω	$V_{GS} = 0V$ , $V_{DS} = 0V$ , $f = 1MHz$	
SWITCHING CHARACTERISTICS (Note 9)							
Total Gate Charge	Qg		6.4		nC	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 5A$	
Total Gate Charge			13			$V_{GS} = 10V, V_{DS} = 15V, I_D = 6.9A$	
Gate-Source Charge	$Q_gs$	_	1.9	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 6.9A$	
Gate-Drain Charge	$Q_{gd}$	_	3.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 6.9A$	
Turn-On Delay Time	t <sub>d(on)</sub>	_	11	_	ns		
Turn-On Rise Time	t <sub>r</sub>	_	7	_	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>d(off)</sub>	_	63	_	ns	$R_D = 1.8\Omega, R_G = 6\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	30	_	ns		

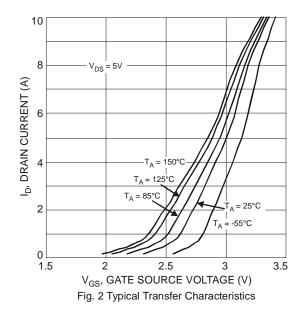
6. Device mounted on 2 oz. Copper pads on FR-4 PCB with  $R_{\theta JA} = 62.5$  °C/W. Notes:

- 7. Pulse width ≤10µS, Duty Cycle ≤1%.
- S. Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.









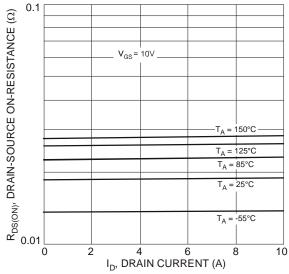
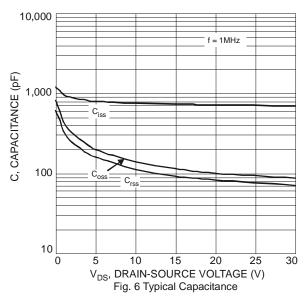
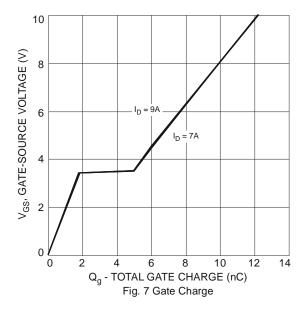


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature







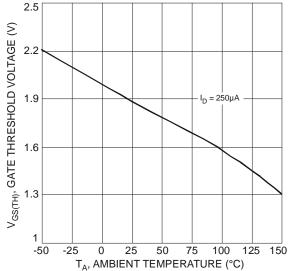
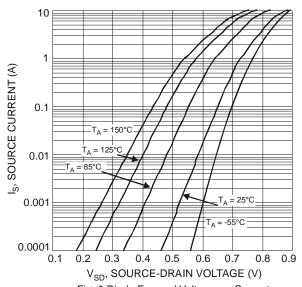


Fig. 8 Gate Threshold Variation vs. Ambient Temperature



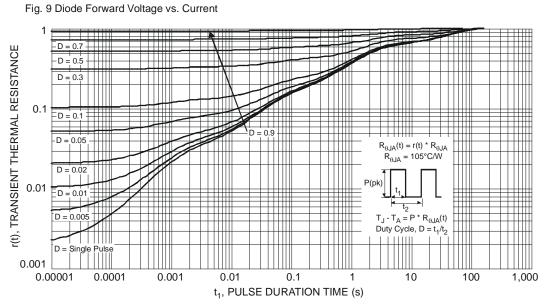
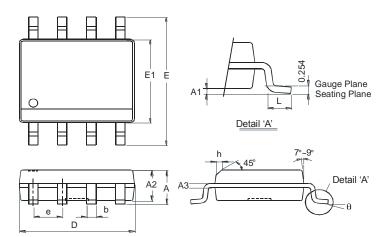


Fig. 10 Transient Thermal Response



### **Package Outline Dimensions**

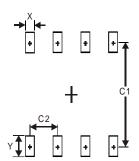
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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